Date Mailed: November 7, 2006

612-455-3801

Sheet 1 of 1

PARAMETER					
FORM 1449* INFORMATION DISCLOSURE STATEMENT	Docket Number: 10873.1623USWO	Application Number: 10/522,488			
· IN AN APPLICATION	Applicant: SASAKI, et al.				
(Use several sheets if necessary)	Filing Date: January 26, 2005	Group Art Unit: 2811			

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RK ·					Ì	YES	NO
	2000-327495	November, 2000	Jepan			Abstract	
RK	2002-293696	October, 2002	Japan	·		Abstract	
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Date Mailed: April 18, 2006

Sheet 1 of 1

FORM 1449* INFORMATION DISCLOSURE STATEMENT	Docket Number: 10873.1623USWO	Application Number: 10/522,488		
IN AN APPLICATION	Applicant: SASAKI, et al.			
(Use several sheets if necessary)	Filing Date: January 26, 2005	Group Art Unit: 2811		

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RK	Yano, et al.	, "Control of Nu	cleation Site and Growth	Orientation of B		Jpn. J. Appl	. Phys. vo	
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FORM 1449\*

## INFORMATION DISCLOSURE STATEMENT

Docket Number: 10873.1623USWO **Application Number:** 

10/522,488

IN AN APPLICATION

Applicant: SASAKI et al.

Filing Date: January 26, 2005

Group Art Unit: Unknown

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(Use several sheets if necessary)

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